

Transforming connectivity with ultra-fast µLEDs

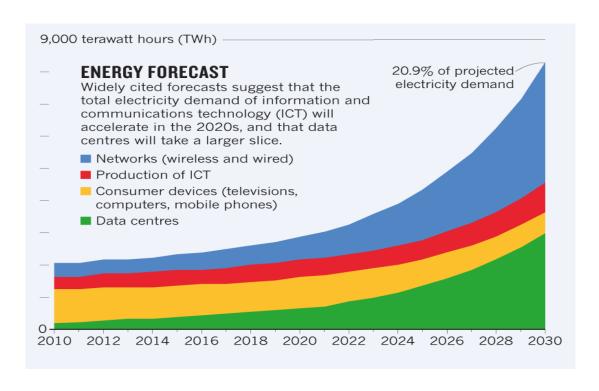
Paradigm Shift in Al Clusters using microLED based Interconnects

Chris Pfistner

Hot Interconnects 2025

Al Networks – Energy Efficiency and Bandwidth Density Needs

IT projected at > 20% of world electricity by 2030



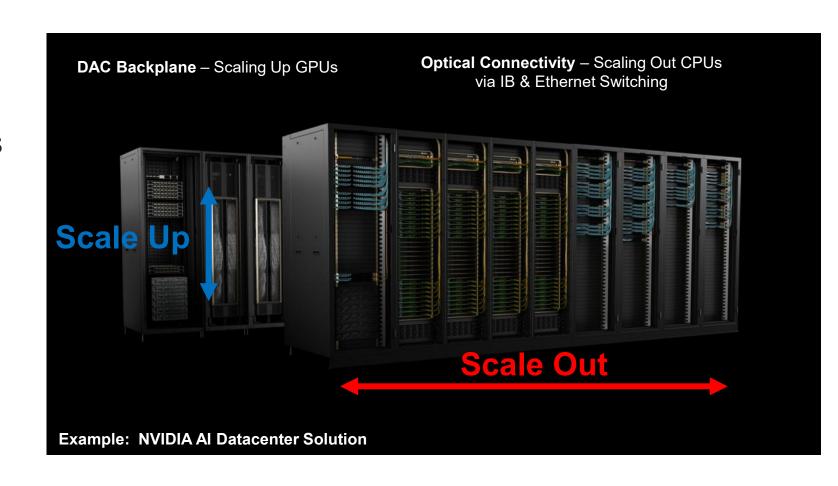
LLM outpacing memory bandwidth 100,000x



Using optimized interconnect technology is absolutely critical!

3 Network Segments in AI – Different Interconnect Technologies

- Inter Datacenter:
 - Transport Networks
- Intra Datacenter:
 - Scale Out:
 - TRV DSP, LRO, LPO
 - □ CPO
 - Scale Up:
 - Today: Copper
 - □ Tomorrow: ???





Exploded View:



Parameter	Performance	
Energy Efficiency *	<< 5pJ/bit	
Shoreline Density	> 1Tbps/mm	
Reach	10m	
Reliability	10 FIT	
Cost Target 2030	\$0.10/Gbps	

^{*} Optical Link including Driver, Laser/LED, PD, TIA, LA

LightBundle:

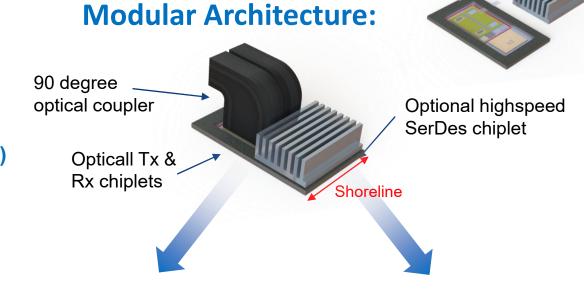
< 1pJ/bit (NRZ format)

1Tbps/mm (2D array)

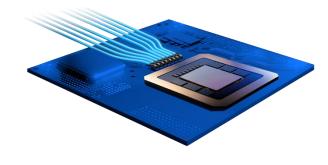
10m - 20m

GaN LEDs:

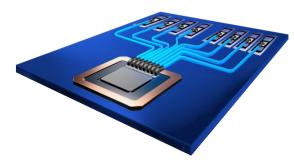
- very reliable
- Op. Temperature: -55° to 125°C
- cost effective



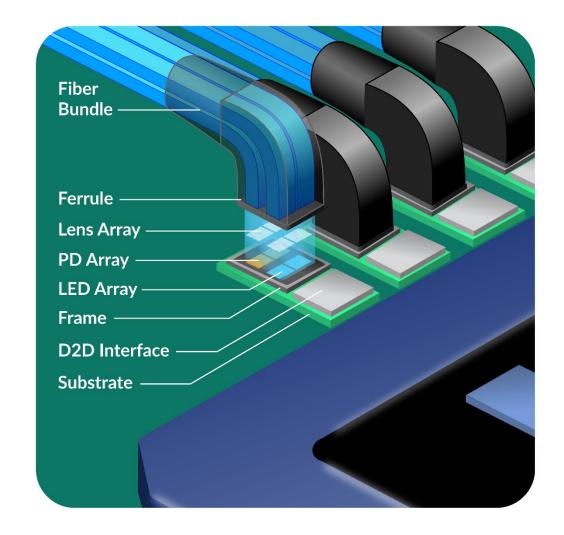
1.6Tbps OBO Module:

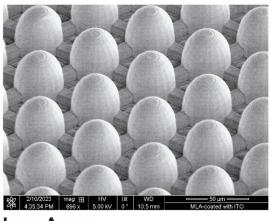


12.8Tbps CPO Module:

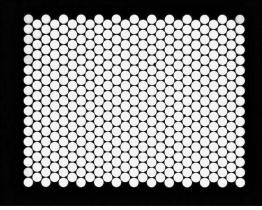


How does the Avicena LightBundleTM solution work

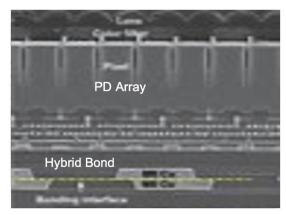




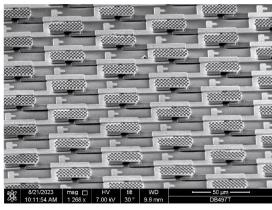
Lens Array



Fiber Bundle Cross Section



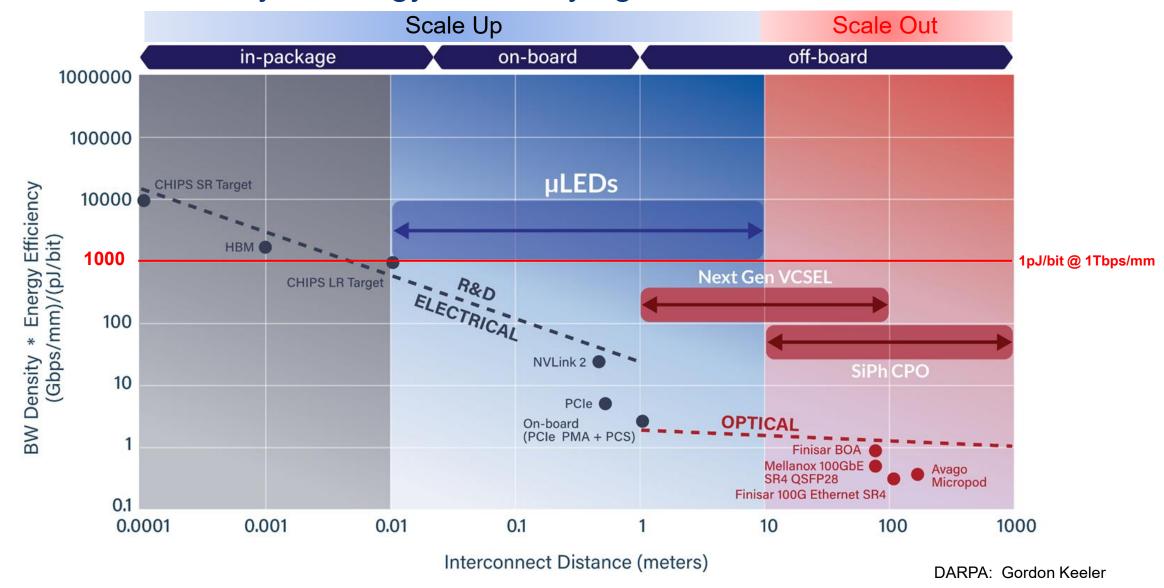
CIS PD Array

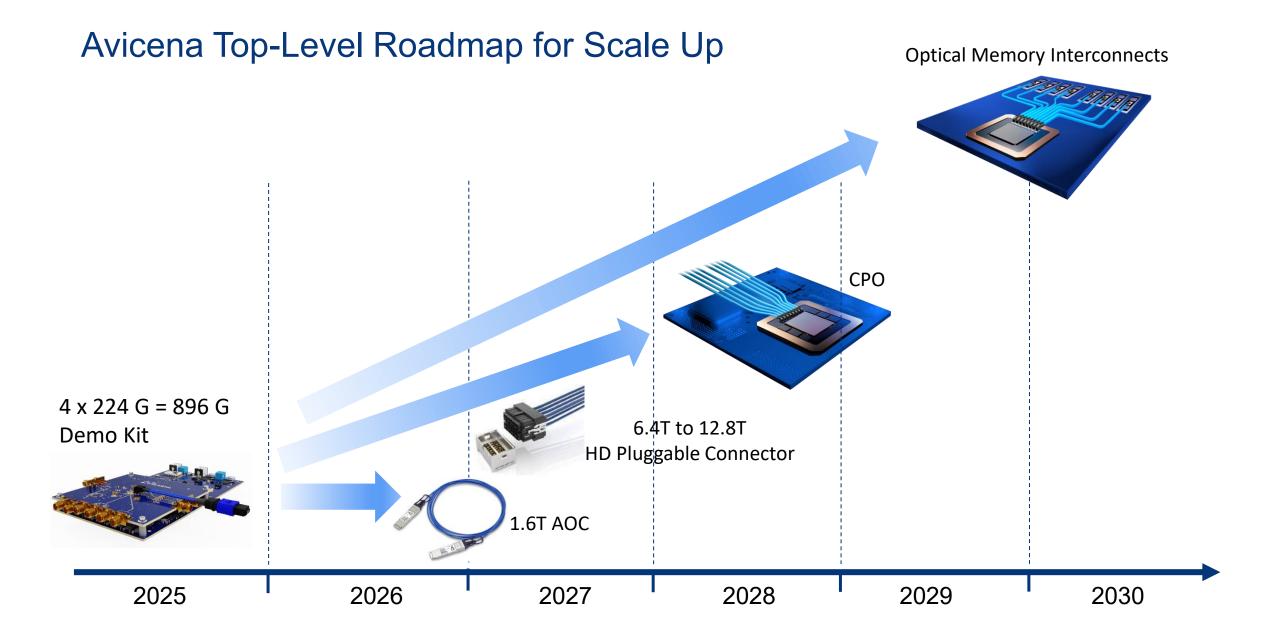


μLED Array



Beach Front Density & Energy Efficiency against Link Distance





Latest Technical Achievements

Demonstrated 16G per lane performance

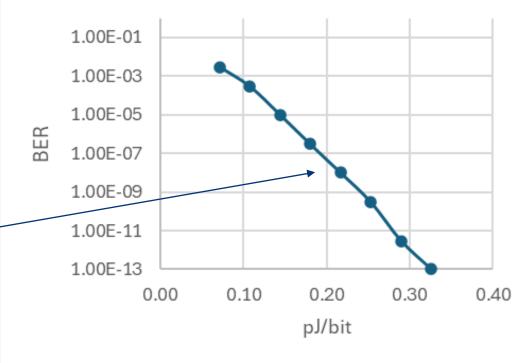
Using TSMC made advanced detectors show ultra-low power single lane performance.

Tx energy efficiency is ~20x better than Silicon Photonics

4Gbps, P_in =3μW, I_LED= 250uA:

• BER~3E-7 @ 0.20pJ/bit

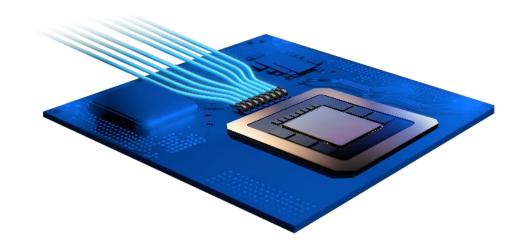
TSMC advanced detector link



Conclusion: µED Interconnects are ideally suited for Scale Up networks

Key Specifications:

Parameter	Performance	Comments
Energy Efficiency	< 1pJ/bit	Incl. Driver, LED, PD, TIA, LA Direct Modulation NRZ
Shoreline Density	> 1Tbps/mm	2D array future: >> 1Tbps/mm
Reach	10m – 20m	Up to 30m with lower energy efficiency
Operating temperature	-55° to 125°C	Demonstrated up to 400°C



Additional Notes:

- 16G per LED demonstrated in our labs July 2025
- GaN LEDs are highly reliable (e.g. lighting industry)
- Compatible with any CMOS process node no specialty foundry required
- Integrated Si PD very well suited for 425nm detection
- Multimode → relaxed assembly tolerances
- Cost effective



Thank You!

